

## ABSTRACT

A method of manufacturing a semiconductor device includes providing a wafer substrate having a surface, forming a first nitride layer over the wafer substrate, providing a layer of photoresist over the first nitride layer, patterning and defining the photoresist layer, etching the first nitride layer unmasked by the photoresist to remove at least a portion of the first nitride layer to expose at least a portion of the substrate surface, removing the photoresist layer, and depositing a second nitride layer over the first nitride layer and the exposed substrate surface to form a nitride structure having a first thickness and a second thickness, wherein the first thickness includes a thickness of the first nitride layer.

FINNEGAN  
HENDERSON  
FARABOW  
GARRETT &  
DUNNER LLP

1300 I Street, NW  
Washington, DC 20005  
202.408.4000  
Fax 202.408.4400  
[www.finnegan.com](http://www.finnegan.com)